

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Maximum Drain Voltage ⁽¹⁾	V _{D,MAX}	650	V
Drain-Gate Voltage (R _{GS} =1MΩ)	V _{DGR}	650	V
Gate-Source (GND) Voltage	V _{GS}	±30	V
Drain Current Pulsed ⁽²⁾	I _{DM}	4.0	ADC
Single Pulsed Avalanche Energy ⁽³⁾	E _{AS}	95	mJ
Continuous Drain Current (T _C =25°C)	I _D	1.0	ADC
Continuous Drain Current (T _C =100°C)	I _D	0.7	ADC
Maximum Supply Voltage	V _{CC,MAX}	30	V
Input Voltage Range	V _{FB}	-0.3 to V _{SD}	V
Total Power Dissipation	P _D	40	W
	Darting	0.32	W/°C
Operating Ambient Temperature	T _A	-25 to +85	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes:

1. T_j = 25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L = 80mH, V_{DD} = 50V, R_G = 27Ω, starting T_j = 25°C

Electrical Characteristics (SFET Part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	VGS=0V, ID=50μA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μA
		VDS=0.8Max., Rating, VGS=0V, TC=125°C	-	-	200	μA
Static Drain-Source on Resistance ^(Note)	RDS(ON)	VGS=10V, ID=0.5A	-	8	10	Ω
Forward Transconductance ^(Note)	gfs	VDS=50V, ID=0.5A	0.5	-	-	S
Input Capacitance	Ciss	VGS=0V, VDS=25V, f=1MHz	-	250	-	pF
Output Capacitance	Coss		-	25	-	
Reverse Transfer Capacitance	Crss		-	10	-	
Turn on Delay Time	td(on)	VDD=0.5B VDS, ID=1.0A (MOSFET switching time is essentially independent of operating temperature)	-	12	-	nS
Rise Time	tr		-	4	-	
Turn off Delay Time	td(off)		-	30	-	
Fall Time	tf		-	10	-	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	VGS=10V, ID=1.0A, VDS=0.5B VDS (MOSFET switching time is essentially independent of operating temperature)	-	-	21	nC
Gate-Source Charge	Qgs		-	3	-	
Gate-Drain (Miller) Charge	Qgd		-	9	-	

Note:

1. Pulse test: Pulse width ≤ 300μS, duty cycle ≤ 2%

2. $S = \frac{1}{R}$

Electrical Characteristics (Control Part) (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start Threshold Voltage	V _{START}	-	14	15	16	V
Stop Threshold Voltage	V _{STOP}	After turn on	9	10	11	V
OSCILLATOR SECTION						
Initial Accuracy	F _{OSC}	Ta=25°C	90	100	110	kHz
Frequency Change With Temperature ⁽²⁾	$\Delta F/\Delta T$	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%
Maximum Duty Cycle	D _{max}	-	64	67	70	%
FEEDBACK SECTION						
Feedback Source Current	I _{FB}	Ta=25°C, 0V ≤ V _{fb} ≤ 3V	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	V _{SD}	-	6.9	7.5	8.1	V
Shutdown Delay Current	I _{delay}	Ta=25°C, 5V ≤ V _{fb} ≤ V _{SD}	4.0	5.0	6.0	μA
SOFT START SECTION (KA1H0165RN)						
Soft Start Voltage	V _{SS}	V _{FB} =2V	4.7	5.0	5.3	V
Soft Start Current	I _{SS}	Sync & S/S=GND	0.8	1.0	1.2	mA
REFERENCE SECTION						
Output Voltage ⁽¹⁾	V _{ref}	Ta=25°C	4.80	5.00	5.20	V
Temperature Stability ⁽¹⁾⁽²⁾	V _{ref} /ΔT	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit	I _{OVER}	Max. inductor current	0.53	0.6	0.67	A
PROTECTION SECTION						
Thermal Shutdown Temperature ⁽¹⁾	T _{SD}	-	140	160	-	°C
Over Voltage Protection Voltage	V _{OV}	-	23	25	28	V
TOTAL DEVICE SECTION						
Start-Up Current	I _{START}	V _{CC} =14V	0.1	0.3	0.4	mA
Operating Supply Current (Control Part Only)	I _{OP}	Ta=25°C	6	12	18	mA
V _{CC} Zener Voltage	V _Z	I _{CC} =20mA	30	32.5	35	V

Note:

1. These parameters, although guaranteed, are not 100% tested in production
2. These parameters, although guaranteed, are tested in EDS (wafer test) process

Typical Performance Characteristics

(These characteristic graphs are normalized at Ta=25°C)

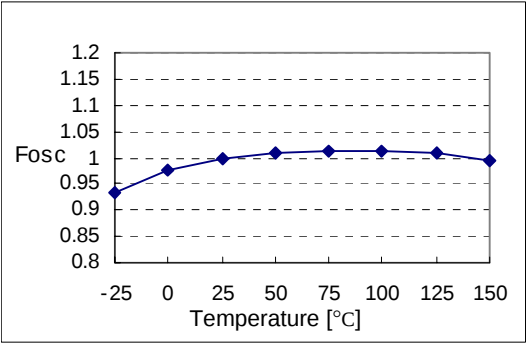


Figure 1. Operating Frequency

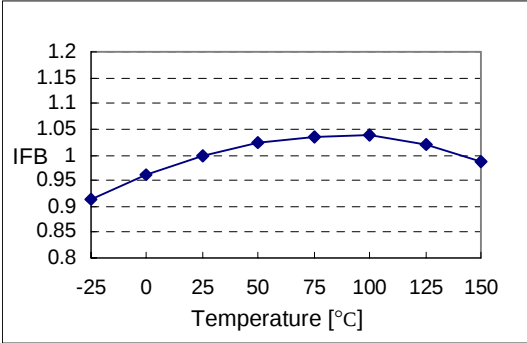


Figure 2. Feedback Source Current

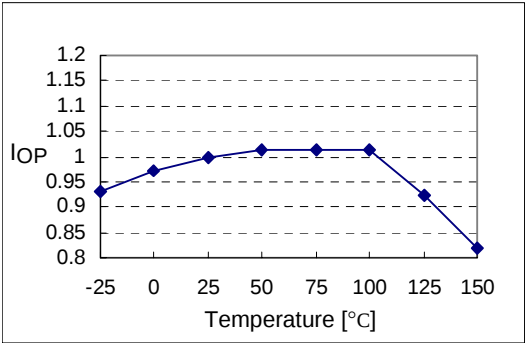


Figure 3. Operating Supply Current

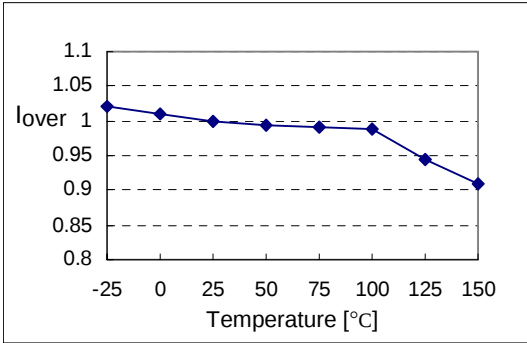


Figure 4. Peak Current Limit

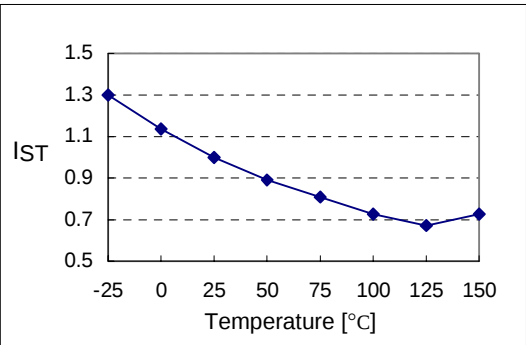


Figure 5. Start up Current

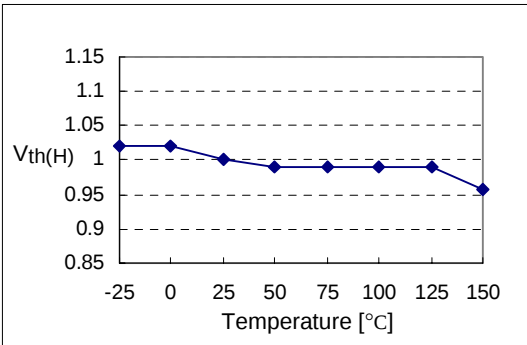


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at $T_a=25^\circ\text{C}$)

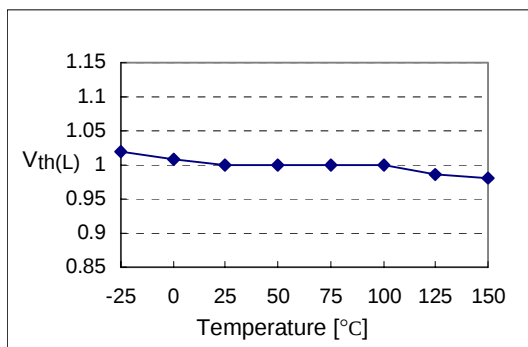


Figure 7. Stop Threshold Voltage

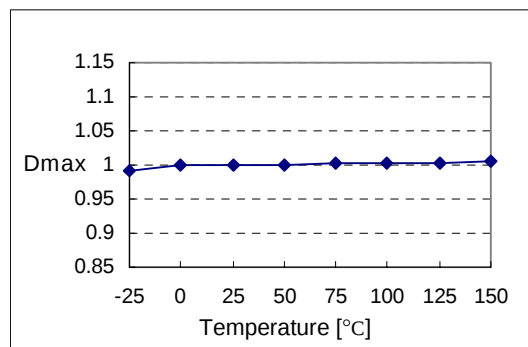


Figure 8. Maximum Duty Cycle

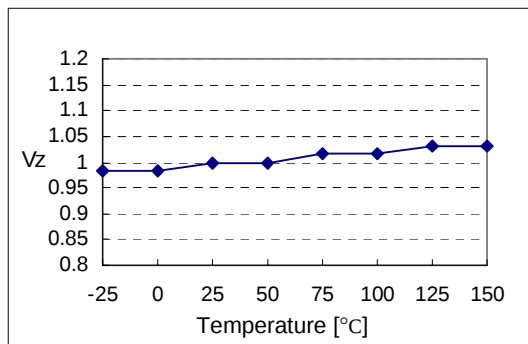


Figure 9. VCC Zener Voltage

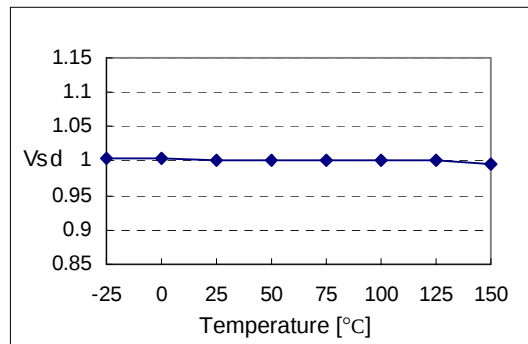


Figure 10. Shutdown Feedback Voltage

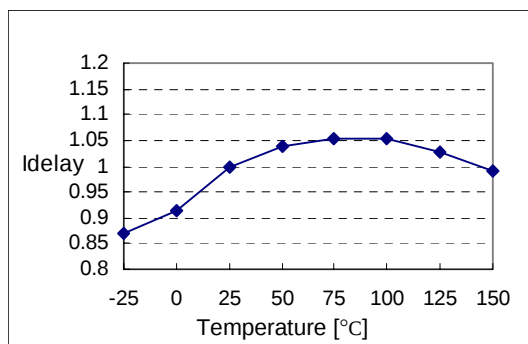


Figure 11. Shutdown Delay Current

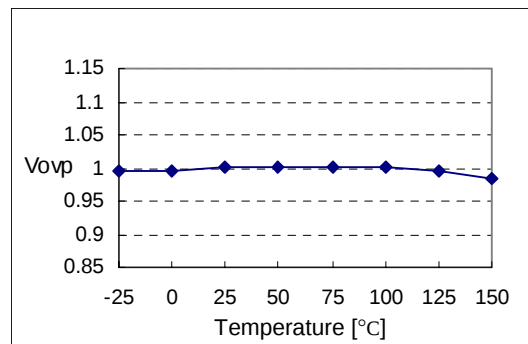


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at $T_a=25^\circ\text{C}$)

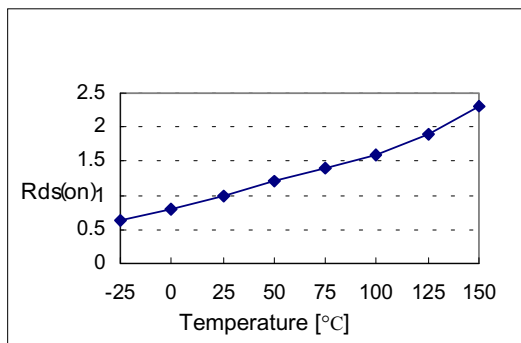
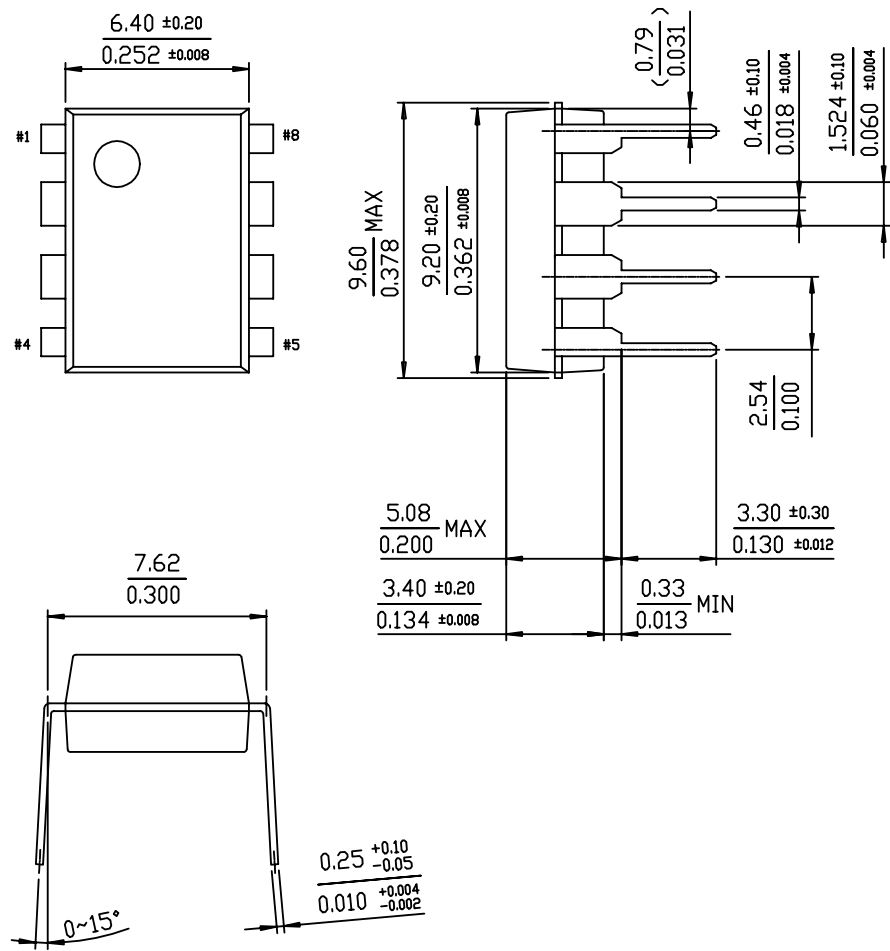


Figure 13. Static Drain-Source on Resistance

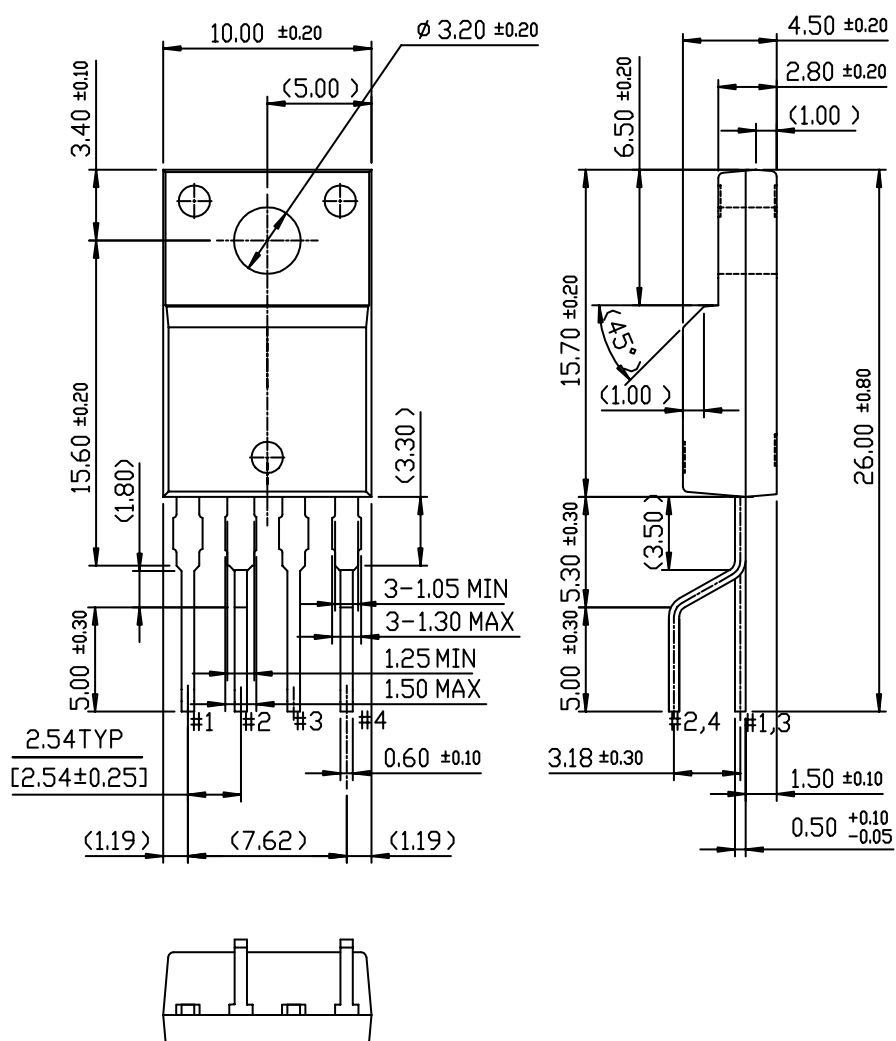
Package Dimensions

8-DIP



Package Dimensions (Continued)

TO-220F-4L(Forming)



Ordering Information

Product Number	Package	Rating	Operating Temperature
KA1H0165RN	8-DIP	650V, 1A	-25°C to +85°C
KA1H0165R-TU	TO-220F-4L	650V, 1A	-25°C to +85°C
KA1H0165R-YDTU			

TU : Non Forming Type

YDTU : Forming Type

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.